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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, LED, POR, PWM, WDT
lumber of I/O	35
Program Memory Size	256KB (256K x 8)
rogram Memory Type	FLASH
EPROM Size	-
AAM Size	40K x 8
oltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
perating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-6
urchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4200f64k256abxqsa1

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Summary of Features

Table 6 SRAM Memory Ranges

Total SRAM Size	Program SRAM	System Data SRAM
40 Kbytes	1FFF C000 _H – 1FFF FFFF _H	2000 0000 _H – 2000 5FFF _H
20 Kbytes	1FFF E000 _H – 1FFF FFFF _H	2000 0000 _H – 2000 2FFF _H

Table 7 ADC Channels¹⁾

Package	VADC G0	VADC G1		
LQFP-64, TQFP-64	CH0, CH3CH7	CH0, CH1, CH3, CH6		
PG-VQFN-48	CH0, CH3CH7	CH0, CH1, CH3		

Some pins in a package may be connected to more than one channel. For the detailed mapping see the Port I/O Function table.

1.6 Identification Registers

The identification registers allow software to identify the marking.

Table 8 XMC4200 Identification Registers

Register Name	Value	Marking
SCU_IDCHIP	0004 2001 _H	EES-AA, ES-AA
SCU_IDCHIP	0004 2002 _H	ES-AB, AB
SCU_IDCHIP	0004 2003 _H	BA
JTAG IDCODE	101D D083 _H	EES-AA, ES-AA
JTAG IDCODE	201D D083 _H	ES-AB, AB
JTAG IDCODE	301D D083 _H	ВА



Summary of Features

Table 9 XMC4100 Identification Registers

Register Name	Value	Marking
SCU_IDCHIP	0004 2001 _H	EES-AA, ES-AA
SCU_IDCHIP	0004 2002 _H	ES-AB, AB
SCU_IDCHIP	0004 1003 _H	BA
JTAG IDCODE	101D D083 _H	EES-AA, ES-AA
JTAG IDCODE	201D D083 _H	ES-AB, AB
JTAG IDCODE	301D D083 _H	ВА



General Device Information

2.2.1 Package Pin Summary

The following general scheme is used to describe each pin:

Table 10 Package Pin Mapping Description

Function	Package A	Package B		Pad Type	Notes
Name	N	Ax		A1+	

The table is sorted by the "Function" column, starting with the regular Port pins (Px.y), followed by the dedicated pins (i.e. PORST) and supply pins.

The following columns, titled with the supported package variants, lists the package pin number to which the respective function is mapped in that package.

The "Pad Type" indicates the employed pad type (A1, A1+, special=special pad, In=input pad, AN/DIG_IN=analog and digital input, Power=power supply). Details about the pad properties are defined in the Electrical Parameters.

In the "Notes", special information to the respective pin/function is given, i.e. deviations from the default configuration after reset. Per default the regular Port pins are configured as direct input with no internal pull device active.

Table 11 Package Pin Mapping

Function	LQFP-64 TQFP-64	VQFN-48	Pad Type	Notes
P0.0	2	2	A1+	
P0.1	1	1	A1+	
P0.2	64	48	A1+	
P0.3	63	47	A1+	
P0.4	62	46	A1+	
P0.5	61	45	A1+	
P0.6	60	44	A1+	
P0.7	58	43	A1+	After a system reset, via HWSEL this pin selects the DB.TDI function.
P0.8	57	42	A1+	After a system reset, via HWSEL this pin selects the DB.TRST function, with a weak pull-down active.
P0.9	4	-	A1+	
P0.10	3	-	A1+	



General Device Information

2.2.2 Port I/O Functions

The following general scheme is used to describe each PORT pin:

Table 12 Port I/O Function Description

Function		Outputs		Inputs			
	ALT1	ALTn	HWO0	HWI0	Input	Input	
P0.0		MODA.OUT	MODB.OUT	MODB.INA	MODC.INA		
Pn.y	MODA.OUT				MODA.INA	MODC.INB	

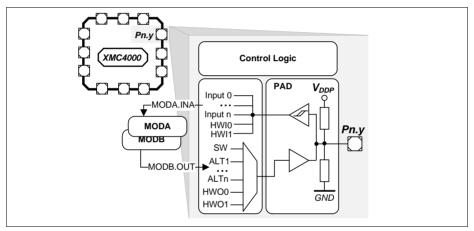


Figure 6 Simplified Port Structure

Pn.y is the port pin name, defining the control and data bits/registers associated with it. As GPIO, the port is under software control. Its input value is read via Pn_IN.y, Pn_OUT defines the output value.

Up to four alternate output functions (ALT1/2/3/4) can be mapped to a single port pin, selected by Pn_IOCR.PC. The output value is directly driven by the respective module, with the pin characteristics controlled by the port registers (within the limits of the connected pad).

The port pin input can be connected to multiple peripherals. Most peripherals have an input multiplexer to select between different possible input sources.

The input path is also active while the pin is configured as output. This allows to feedback an output to on-chip resources without wasting an additional external pin.

By Pn_HWSEL it is possible to select between different hardware "masters" (HWO0/HWI0). The selected peripheral can take control of the pin(s). Hardware control overrules settings in the respective port pin registers.

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XMC4100 / XMC4200 XMC4000 Family

Infineon

Port I/O Functions (CONt'd) Table 13

Function		Output					Input							
	ALT1	ALT2	ALT3	ALT4	HWO0	HWI0	Input	Input	Input	Input	Input	Input	Input	Input
P1.8		U0C0. SELO1		U1C1. SCLKOUT										
P1.9	U0C0. SCLKOUT			U1C1. DOUT0										
P1.15	SCU. EXTCLK			U1C0. DOUT0						ERU1. 1A0				
P2.0	CAN. N0_TXD			LEDTS0. COL1					ERU0. 0B3		CCU40. IN1C			
P2.1				LEDTS0. COL0	DB.TDO/ TRACESWO					ERU1. 0B0	CCU40. INOC			
P2.2	VADC. EMUX00		CCU41. OUT3	LEDTS0. LINE0	LEDTS0. EXTENDED0	LEDTS0. TSIN0A		U0C1. DX0A	ERU0. 1B2		CCU41. IN3A			
P2.3	VADC. EMUX01	U0C1. SELO0	CCU41. OUT2	LEDTS0. LINE1	LEDTS0. EXTENDED1	LEDTS0. TSIN1A		U0C1. DX2A	ERU0. 1A2		CCU41. IN2A			
P2.4	VADC. EMUX02	U0C1. SCLKOUT	CCU41. OUT1	LEDTS0. LINE2	LEDTS0. EXTENDED2	LEDTS0. TSIN2A		U0C1. DX1A	ERU0. 0B2		CCU41. IN1A	HRPWM0. BL1A		
P2.5		U0C1. DOUT0	CCU41. OUT0	LEDTS0. LINE3	LEDTS0. EXTENDED3	LEDTS0. TSIN3A		U0C1. DX0B	ERU0. 0A2		CCU41. INOA	HRPWM0. BL2A		
P2.6			CCU80. OUT13	LEDTS0. COL3				CAN. N1_RXDA	ERU0. 1B3		CCU40. IN3C			
P2.7		CAN. N1_TXD	CCU80. OUT03	LEDTS0. COL2						ERU1. 1B0	CCU40. IN2C			
P2.8			CCU80. OUT32	LEDTS0. LINE4	LEDTS0. EXTENDED4	LEDTS0. TSIN4A	DAC. TRIGGER5				CCU40. IN0B	CCU40. IN1B	CCU40. IN2B	CCU40. IN3B
P2.9			CCU80. OUT22	LEDTS0. LINE5	LEDTS0. EXTENDED5	LEDTS0. TSIN5A	DAC. TRIGGER4				CCU41. IN0B	CCU41. IN1B	CCU41. IN2B	CCU41. IN3B
P2.14	VADC. EMUX11	U1C0. DOUT0	CCU80. OUT21					U1C0. DX0D						
P2.15	VADC. EMUX12		CCU80. OUT11	LEDTS0. LINE6	LEDTS0. EXTENDED6	LEDTS0. TSIN6A		U1C0. DX0C						
P3.0		U0C1. SCLKOUT					U0C1. DX1B				CCU80. IN2C			
P14.0							VADC. G0CH0							
P14.3							VADC. G0CH3	VADC. G1CH3			CAN. N0_RXDB			
P14.4							VADC. G0CH4							
P14.5							VADC. G0CH5				POSIF0. IN2B			
P14.6							VADC. G0CH6				POSIF0. IN1B		G0ORC6	
214.7							VADC. G0CH7				POSIF0. IN0B			
14.8					DAC. OUT_0			VADC. G1CH0						



2.3 Power Connection Scheme

Figure 7. shows a reference power connection scheme for the XMC4[12]00.

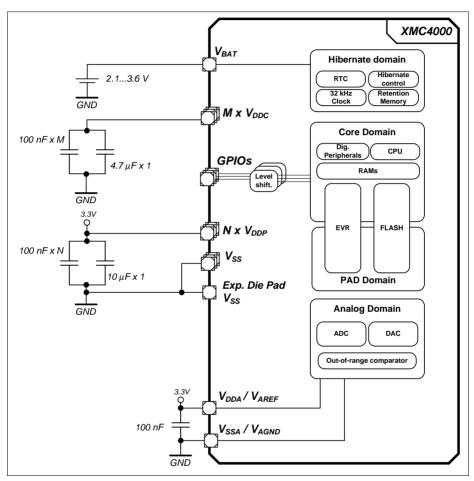


Figure 7 Power Connection Scheme

Every power supply pin needs to be connected. Different pins of the same supply need also to be externally connected. As example, all $V_{\rm DDP}$ pins must be connected externally to one $V_{\rm DDP}$ net. In this reference scheme one 100 nF capacitor is connected at each supply pin against $V_{\rm SS}$. An additional 10 µF capacitor is connected to the $V_{\rm DDP}$ nets and an additional 4.7uF capacitor to the $V_{\rm DDC}$ nets.



3 Electrical Parameters

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section partly represent the characteristics of the XMC4[12]00 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are marked with an two-letter abbreviation in column "Symbol":

- CC
 - Such parameters indicate Controller Characteristics, which are a distinctive feature of the XMC4[12]00 and must be regarded for system design.
- SR

Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC4[12]00 is designed in.



3.1.3 Pin Reliability in Overload

When receiving signals from higher voltage devices, low-voltage devices experience overload currents and voltages that go beyond their own IO power supplies specification.

Table 15 defines overload conditions that will not cause any negative reliability impact if all the following conditions are met:

- · full operation life-time is not exceeded
- Operating Conditions are met for
 - pad supply levels (V_{DDP} or V_{DDA})
 - temperature

If a pin current is outside of the **Operating Conditions** but within the overload parameters, then the parameters functionality of this pin as stated in the Operating Conditions can no longer be guaranteed. Operation is still possible in most cases but with relaxed parameters.

Note: An overload condition on one or more pins does not require a reset.

Note: A series resistor at the pin to limit the current to the maximum permitted overload current is sufficient to handle failure situations like short to battery.

Table 15 Overload Parameters

Parameter	Syml	Symbol		Values	5	Unit	Note /
			Min.	Тур.	Max.		Test Condition
Input current on any port pin during overload condition	I_{OV}	SR	-5	-	5	mA	
Absolute sum of all input circuit currents for one port	I_{OVG}	SR	_	_	20	mA	$\Sigma I_{\rm OVx} $, for all $I_{\rm OVx} < 0$ mA
group during overload condition ¹⁾			_	_	20	mA	$\Sigma I_{\rm OVx} $, for all $I_{\rm OVx} > 0$ mA
Absolute sum of all input circuit currents during overload condition	I_{OVS}	SR	_	_	80	mA	ΣI_{OVG}

¹⁾ The port groups are defined in Table 18.

Figure 9 shows the path of the input currents during overload via the ESD protection structures. The diodes against $V_{\rm DDP}$ and ground are a simplified representation of these ESD protection structures.



3.1.4 Pad Driver and Pad Classes Summary

This section gives an overview on the different pad driver classes and its basic characteristics. More details (mainly DC parameters) are defined in the **Section 3.2.1**.

Table 19 Pad Driver and Pad Classes Overview

Class	Power Supply	Туре	Sub-Class	Speed Grade	Load	Termination
Α	3.3 V LVTTL I/O,		A1 (e.g. GPIO)	6 MHz	100 pF	No
		LVTTL outputs	A1+ (e.g. serial I/Os)	25 MHz	50 pF	Series termination recommended

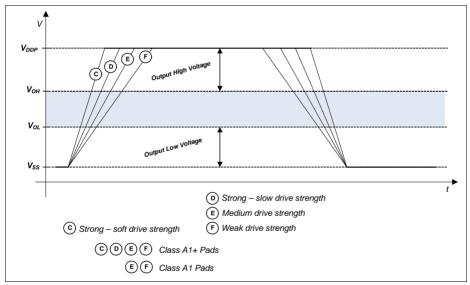


Figure 10 Output Slopes with different Pad Driver Modes

Figure 10 is a qualitative display of the resulting output slope performance with different output driver modes. The detailed input and output characteristics are listed in Section 3.2.1.



3.2 DC Parameters

3.2.1 Input/Output Pins

The digital input stage of the shared analog/digital input pins is identical to the input stage of the standard digital input/output pins.

The pull-up characteristics ($I_{\rm PUH}$) and the input high and low voltage levels ($V_{\rm IH}$ and $V_{\rm IL}$) of the PORST pin are identical to the respective values of the standard digital input/output pins.

Table 21 Standard Pad Parameters

Parameter	Symbol	Va	alues	Unit	Note / Test Condition
		Min.	Max.		
Pin capacitance (digital inputs/outputs)	$C_{IO}CC$	_	10	pF	
Pull-down current	$ I_{PDL} $	150	_	μΑ	$^{1)}V_{IN} \geq 0.6 imes V_{DDP}$
	SR	_	10	μΑ	$^{2)}V_{IN} \leq 0.36 \times V_{DDP}$
Pull-up current	$ I_{\mathrm{PUH}} $ SR	_	10	μΑ	$^{2)}V_{IN} \geq 0.6 imes V_{DDP}$
		100	_	μΑ	$^{1)}V_{IN} \leq 0.36 \times V_{DDP}$
Input Hysteresis for pads of all A classes ³⁾	HYSA CC	0.1 × <i>V</i> _{DDP}	-	V	
PORST spike filter always blocked pulse duration	t _{SF1} CC	_	10	ns	
PORST spike filter pass-through pulse duration	t _{SF2} CC	100	-	ns	
PORST pull-down current	$ I_{\rm PPD} $ CC	13	-	mA	V _i = 1.0 V

Current required to override the pull device with the opposite logic level ("force current").
 With active pull device, at load currents between force and keep current the input state is undefined.

Load current at which the pull device still maintains the valid logic level ("keep current").
 With active pull device, at load currents between force and keep current the input state is undefined.

³⁾ Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.



Table 23 Standard Pads Class_A1+

Parameter	Symbol	Va	lues	Unit	Note /
		Min.	Max.		Test Condition
Output high voltage,	V_{OHA1+}	V_{DDP} - 0.4	_	V	$I_{OH} \geq$ -400 μA
POD ¹⁾ = weak	CC	2.4	-	V	$I_{OH} \ge$ -500 μA
Output high voltage,		V _{DDP} - 0.4	-	V	$I_{OH} \geq$ -1.4 mA
POD ¹⁾ = medium		2.4	_	V	$I_{OH} \ge$ -2 mA
Output high voltage,		V_{DDP} - 0.4	_	V	$I_{\mathrm{OH}} \geq$ -1.4 mA
POD ¹⁾ = strong		2.4	_	V	$I_{OH} \ge$ -2 mA
Output low voltage	V_{OLA1+}	_	0.4	V	$I_{OL} \le 500 \mu A;$ POD ¹⁾ = weak
		_	0.4	V	$I_{OL} \le 2 \text{ mA};$ POD ¹⁾ = medium
		-	0.4	V	$I_{OL} \le 2 \text{ mA};$ POD ¹⁾ = strong
Fall time	t _{FA1+} CC	-	150	ns	$C_L = 20 \text{ pF};$ POD ¹⁾ = weak
		-	50	ns	$C_L = 50 \text{ pF};$ POD ¹⁾ = medium
		_	28	ns	C_{L} = 50 pF; POD ¹⁾ = strong; edge = slow
		_	16	ns	C_L = 50 pF; POD ¹⁾ = strong; edge = soft;
Rise time	t _{RA1+} CC	-	150	ns	$C_L = 20 \text{ pF};$ POD ¹⁾ = weak
		-	50	ns	$C_L = 50 \text{ pF};$ POD ¹⁾ = medium
		_	28	ns	C_{L} = 50 pF; POD ¹⁾ = strong; edge = slow
		_	16	ns	C_L = 50 pF; POD ¹⁾ = strong; edge = soft

¹⁾ POD = Pin Out Driver



 Table 27
 DAC Parameters (Operating Conditions apply) (cont'd)

Parameter	Symbo	Symbol		Values	3	Unit	Note /
			Min.	Тур.	Max.		Test Condition
Offset error	ED_{OFF}	CC		±20		mV	
Gain error	ED_{G_IN}	CC	-5	0	5	%	
Startup time	t _{STARTU}	-CC	_	15	30	μS	time from output enabling till code valid ±16 LSB
3dB Bandwidth of Output Buffer	f_{C1}	СС	2.5	5	_	MHz	verified by design
Output sourcing current	I _{OUT_SO}	URCE	_	-30	_	mA	
Output sinking current	I _{OUT_SIN}	IK	_	0.6	_	mA	
Output resistance	R_{OUT}	CC	-	50	_	Ohm	
Load resistance	R_{L}	SR	5	-	-	kOhm	
Load capacitance	C_{L}	SR	-	-	50	pF	
Signal-to-Noise Ratio	SNR	СС	_	70	-	dB	examination bandwidth < 25 kHz
Total Harmonic Distortion	THD	CC	_	70	_	dB	examination bandwidth < 25 kHz
Power Supply Rejection Ratio	PSRR	СС	_	56	_	dB	to $V_{\rm DDA}$ verified by design

¹⁾ According to best straight line method.

Conversion Calculation

Unsigned:

 $\mathsf{DACxDATA} = 4095 \times (V_{\mathsf{OUT}} - V_{\mathsf{OUT}\ \mathsf{MIN}}) \, / \, (V_{\mathsf{OUT}\ \mathsf{MAX}} - V_{\mathsf{OUT}\ \mathsf{MIN}})$

Signed:

 $\mathsf{DACxDATA} = 4095 \times (V_\mathsf{OUT} - V_\mathsf{OUT_MIN}) \, / \, (V_\mathsf{OUT_MAX} - V_\mathsf{OUT_MIN}) \, - \, 2048$



Table 32 External clock operating conditions

Parameter	Symbol		Value	Unit	Note /	
		Min.	Тур.	Max.		Test Con dition
Frequency	$f_{ m eclk}$ SR	_	_	$f_{\text{hrpwm}}/4$	MHz	
ON time	t _{oneclk} SR	$2T_{\rm ccu}^{-1)2)}$	_	_	ns	
OFF time	$t_{ m offeclk}$ SR	$2T_{\rm ccu}^{-1)2)}$	_	_	ns	Only the rising edge is used

^{1) 50%} duty cycle is not obligatory

3.2.6 Low Power Analog Comparator (LPAC)

The Low Power Analog Comparator (LPAC) triggers a wake-up event from Hibernate state or an interrupt trigger during normal operation. It does so by comparing $V_{\rm BAT}$ or another external sensor voltage $V_{\rm LPS}$ with a pre-programmed threshold voltage.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 33 Low Power Analog Comparator Parameters

Parameter	Symbol		Values	}	Unit	Note /
		Min.	Тур.	Max.		Test Condition
V_{BAT} supply voltage range for LPAC operation	V_{BAT} SR	2.1	_	3.6	V	
Sensor voltage range	V_{LPCS}	0	_	1.2	V	
Threshold step size	V_{th} CC	_	18.75	_	mV	
Threshold trigger accuracy	$\varDelta V_{th}$ CC	_	-	±10	%	for V_{th} > 0.4 V
Conversion time	t_{LPCC} CC	_	_	250	μS	
Average current consumption over time	I _{LPCAC} CC	_	_	15	μΑ	conversion interval 10 ms ¹⁾
Current consumption during conversion	I_{LPCC} CC	_	150	_	μΑ	1)

¹⁾ Single channel conversion, measuring $V_{\rm BAT}$ = 3.3 V, 8 cycles settling time

²⁾ Only valid if the signal was not previously synchronized/generated with the fccu clock (or a synchronous clock)



Table 36 OSC_XTAL Parameters

Parameter	ameter Symbol Values			Unit	Note /		
		Min.	Тур.	Max.		Test Condition	
Input frequency	$f_{ m OSC}{ m SR}$	4	_	40	MHz	Direct Input Mode selected	
		4	_	25	MHz	External Crystal Mode selected	
Oscillator start-up time ¹⁾²⁾	t _{OSCS} CC	_	_	10	ms		
Input voltage at XTAL1	V_{IX} SR	-0.5	_	V _{DDP} + 0.5	V		
Input amplitude (peak-to-peak) at XTAL1 ²⁾³⁾	$V_{PPX}SR$	V_{DDP}	_	V _{DDP} + 1.0	V		
Input high voltage at XTAL1 ⁴⁾	$V_{IHBX}SR$	1.0	_	V _{DDP} + 0.5	V		
Input low voltage at XTAL1 ⁴⁾	$V_{ILBX}SR$	-0.5	_	0.4	V		
Input leakage current at XTAL1	I _{ILX1} CC	-100	_	100	nA		

¹⁾ $t_{\rm OSCS}$ is defined from the moment the oscillator is enabled wih SCU_OSCHPCTRL.MODE until the oscillations reach an amplitude at XTAL1 of 0.4 * $V_{\rm DDP}$.

²⁾ The external oscillator circuitry must be optimized by the customer and checked for negative resistance and amplitude as recommended and specified by crystal suppliers.

³⁾ If the shaper unit is enabled and not bypassed.

⁴⁾ If the shaper unit is bypassed, dedicated DC-thresholds have to be met.



Table 38 Power Supply Parameters

Parameter	Symb	Symbol		Value	s	Unit	Note /
			Min.	Тур.	Max.		Test Condition
Power Dissipation	P_{DISS}	CC	_	-	1	W	$V_{\rm DDP} = 3.6 \text{ V},$ $T_{\rm J} = 150 ^{\circ}\text{C}$
Wake-up time from Sleep to Active mode	t_{SSA}	CC	_	6	_	cycles	
Wake-up time from Deep Sleep to Active mode			-	_	-	ms	Defined by the wake-up of the Flash module, see Section 3.2.11
Wake-up time from Hibernate mode			_	_	-	ms	Wake-up via power-on reset event, see Section 3.3.2

- 1) CPU executing code from Flash, all peripherals idle.
- 2) CPU executing code from Flash. USB and CCU clock off.
- 3) CPU in sleep, all peripherals idle, Flash in Active mode.
- 4) CPU in sleep, Flash in Active mode.
- 5) CPU in sleep, peripherals disabled, after wake-up code execution from RAM.
- 6) To wake-up the Flash from its Sleep mode, $f_{CPII} \ge 1$ MHz is required.
- 7) OSC_ULP operating with external crystal on RTC_XTAL
- 8) OSC_ULP off, Hibernate domain operating with OSC_SI clock
- 9) Test Power Loop: f_{SYS} = 80 MHz, CPU executing benchmark code from Flash, all CCUs in 100kHz timer mode, all ADC groups in continuous conversion mode, USICs as SPI in internal loop-back mode, CAN in 500kHz internal loop-back mode, interrupt triggered DMA block transfers to parity protected RAMs and FCE, DTS measurements and FPU calculations.
 - The power consumption of each customer application will most probably be lower than this value, but must be evaluated separately.
- 10) $I_{\rm DDP}$ decreases typically by 3.5 mA when $f_{\rm SYS}$ decreases by 10 MHz, at constant $T_{\rm J}$
- 11) Sum of currents of all active converters (ADC and DAC)



3.3.7 Serial Wire Debug Port (SW-DP) Timing

The following parameters are applicable for communication through the SW-DP interface.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Note: Operating conditions apply.

 Table 47
 SWD Interface Timing Parameters (Operating Conditions apply)

Parameter		nbol		Values	3	Unit	Note /
			Min.	Тур.	Max.		Test Condition
SWDCLK clock period	t_{SC}	SR	25	_	_	ns	C _L = 30 pF
			40	-	_	ns	C _L = 50 pF
SWDCLK high time	t_1	SR	10	-	500000	ns	
SWDCLK low time	t_2	SR	10	-	500000	ns	
SWDIO input setup to SWDCLK rising edge	<i>t</i> ₃	SR	6	_	_	ns	
SWDIO input hold after SWDCLK rising edge	t_4	SR	6	-	_	ns	
SWDIO output valid time	t_5	CC	_	-	17	ns	C _L = 50 pF
after SWDCLK rising edge			_	-	13	ns	C _L = 30 pF
SWDIO output hold time from SWDCLK rising edge	<i>t</i> ₆	CC	3	-	_	ns	

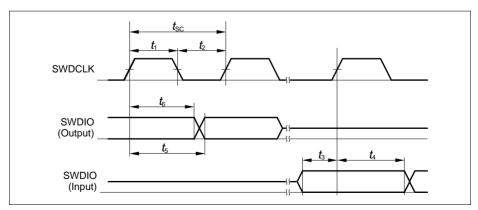


Figure 30 SWD Timing

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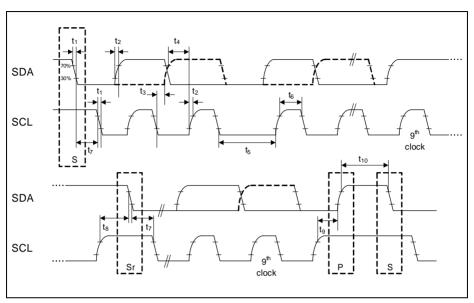


Figure 32 USIC IIC Stand and Fast Mode Timing

3.3.8.3 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: Operating Conditions apply.

Table 52 USIC IIS Master Transmitter Timing

Parameter	Symbol		Values	3	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Clock period	t ₁ CC	33.3	-	_	ns	
Clock high time	t ₂ CC	0.35 x	_	_	ns	
		t_{1min}				
Clock low time	t ₃ CC	0.35 x	_	_	ns	
		t_{1min}				
Hold time	t ₄ CC	0	_	_	ns	
Clock rise time	t ₅ CC	-	_	0.15 x	ns	
				t_{1min}		



3.3.9 USB Interface Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification. High-Speed Mode is not supported.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

 Table 54
 USB Timing Parameters (operating conditions apply)

Parameter	Symbol			Value	s	Unit	Note /
			Min.	Тур.	Max.		Test Condition
Rise time	t_{R}	CC	4	_	20	ns	$C_L = 50 \text{ pF}$
Fall time	t_{F}	CC	4	_	20	ns	$C_L = 50 \text{ pF}$
Rise/Fall time matching	$t_{\rm R}/t_{\rm F}$	CC	90	-	111.11	%	C _L = 50 pF
Crossover voltage	V_{CRS}	CC	1.3	_	2.0	V	C _L = 50 pF

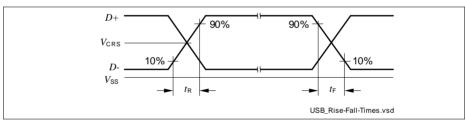


Figure 35 USB Signal Timing



Package and Reliability

4.2 Package Outlines

The availability of different packages for different devices types is listed in **Table 1**, specific packages for different device markings are listed in **Table 2**.

The exposed die pad dimensions are listed in Table 55.

Table 56 Differences PG-LQFP-64-19 to PG-TQFP-64-19

Change	PG-LQFP-64-19	PG-TQFP-64-19
Thermal Resistance Junction Ambient $(R_{\Theta JA})$	30 K/W	23.4 K/W
Package thickness	1.4 ^{±0.05} mm	1.0 ^{±0.05} mm
	1.6 mm MAX	1.2 mm MAX
Exposed Die Pad size	5.8 mm × 5.8 mm	5.7 mm × 5.7 mm



Quality Declarations

5 Quality Declarations

The qualification of the XMC4[12]00 is executed according to the JEDEC standard JESD47H.

Note: For automotive applications refer to the Infineon automotive microcontrollers.

Table 58 Quality Parameters

Parameter	Symbol		Values	3	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Operation lifetime	t _{OP} CC	20	_	-	а	$T_{\rm J} \le 109 ^{\rm o}{\rm C},$ device permanent on
ESD susceptibility according to Human Body Model (HBM)	V _{HBM} SR	_	_	2 000	V	EIA/JESD22- A114-B
ESD susceptibility according to Charged Device Model (CDM)	V_{CDM} SR	_	_	500	V	Conforming to JESD22-C101-C
Moisture sensitivity level	MSL CC	_	-	3	_	JEDEC J-STD-020D
Soldering temperature	T _{SDR} SR	_	_	260	°C	Profile according to JEDEC J-STD-020D